

# Complementary Power Transistors

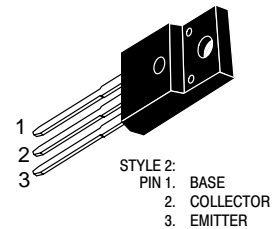
## For Isolated Package Applications

Designed for general-purpose amplifier and switching applications, where the mounting surface of the device is required to be electrically isolated from the heatsink or chassis.

- Electrically Similar to the Popular MJE15030 and MJE15031
- 150 V<sub>CEO(sus)</sub>
- 8 A Rated Collector Current
- No Isolating Washers Required
- Reduced System Cost
- High Current Gain-Bandwidth Product
 
$$f_T = 30 \text{ MHz (Min) @ } I_C = 500 \text{ mA}$$
- UL Recognized, File #E69369, to 3500 V<sub>RMS</sub> Isolation

**NPN**  
**MJF15030**  
**PNP**  
**MJF15031**

**COMPLEMENTARY**  
**SILICON**  
**POWER TRANSISTORS**  
**8 AMPERES**  
**150 VOLTS**  
**36 WATTS**



**CASE 221D-02**  
**TO-220 TYPE**

# MJF15030 MJF15031

## MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	$V_{CEO}$	150	Vdc
Collector–Base Voltage	$V_{CB}$	150	Vdc
Emitter–Base Voltage	$V_{EB}$	5	Vdc
RMS Isolation Voltage (1) (for 1 sec, R.H. < 30%, $T_A = 25^\circ\text{C}$ )	$V_{ISOL}$	4500 3500 1500	$V_{RMS}$
Collector Current — Continuous — Peak	$I_C$	8 16	Adc
Base Current	$I_B$	2	Adc
Total Power Dissipation* @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	36 0.29	Watts $W/^\circ\text{C}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	2 0.016	Watts $W/^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case*	$R_{\theta JC}$	3.5	$^\circ\text{C/W}$
Lead Temperature for Soldering Purpose	$T_L$	260	$^\circ\text{C}$

\*Measurement made with thermocouple contacting the bottom insulated mounting surface (in a location beneath the die), the device mounted on a heatsink with thermal grease and a mounting torque of  $\geq 6$  in. lbs.

(1) Proper strike and creepage distance must be provided.

## ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Collector–Emitter Sustaining Voltage (1) ( $I_C = 10$ mAdc, $I_B = 0$ )	$V_{CEO(sus)}$	150	—	Vdc
Collector Cutoff Current ( $V_{CE} = 150$ Vdc, $I_B = 0$ )	$I_{CEO}$	—	10	$\mu\text{Adc}$
Collector Cutoff Current ( $V_{CB} = 150$ Vdc, $I_E = 0$ )	$I_{CBO}$	—	10	$\mu\text{Adc}$
Emitter Cutoff Current ( $V_{BE} = 5$ Vdc, $I_C = 0$ )	$I_{EBO}$	—	10	$\mu\text{Adc}$

## ON CHARACTERISTICS (1)

DC Current Gain ( $I_C = 0.1$ Adc, $V_{CE} = 2$ Vdc) ( $I_C = 2$ Adc, $V_{CE} = 2$ Vdc) ( $I_C = 3$ Adc, $V_{CE} = 2$ Vdc) ( $I_C = 4$ Adc, $V_{CE} = 2$ Vdc)	$h_{FE}$	40 40 40 20	— — — —	—
DC Current Gain Linearity ( $V_{CE}$ from 2 V to 20 V, $I_C$ from 0.1 A to 3 A) (NPN to PNP)	$h_{FE}$	<b>Typ</b> 2 3		
Collector–Emitter Saturation Voltage ( $I_C = 1$ Adc, $I_B = 0.1$ Adc)	$V_{CE(sat)}$	—	0.5	Vdc
Base–Emitter On Voltage ( $I_C = 1$ Adc, $V_{CE} = 2$ Vdc)	$V_{BE(on)}$	—	1	Vdc

## DYNAMIC CHARACTERISTICS

Current Gain–Bandwidth Product (2) ( $I_C = 500$ mAdc, $V_{CE} = 10$ Vdc, $f_{test} = 10$ MHz)	$f_T$	30	—	MHz
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### NOTES:

1. Pulse Test: Pulse Width  $\leq 300$   $\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .
2.  $f_T = |h_{fe}| \cdot f_{test}$ .

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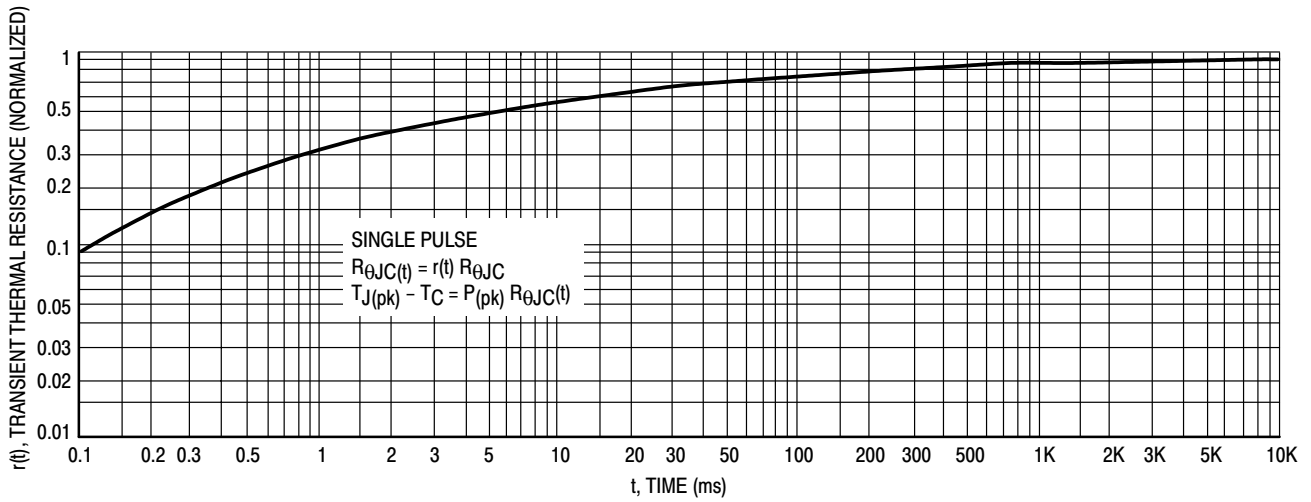


Figure 1. Thermal Response

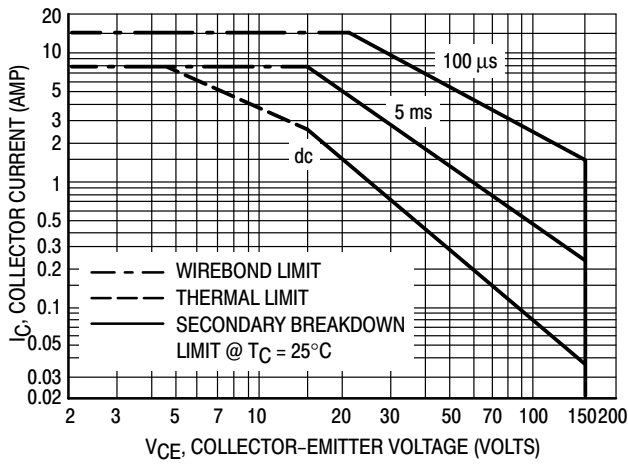
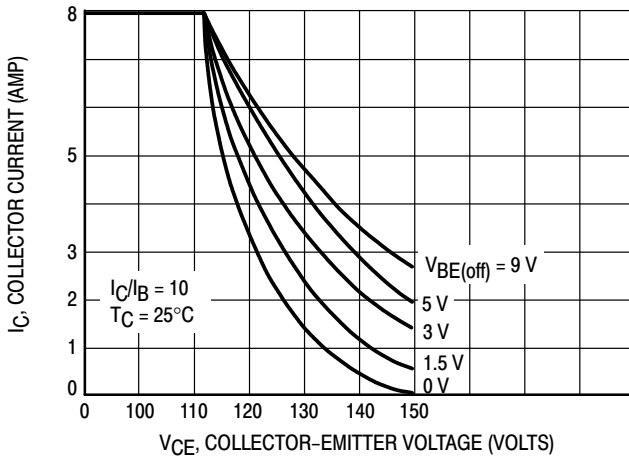


Figure 2. Forward Bias Safe Operating Area

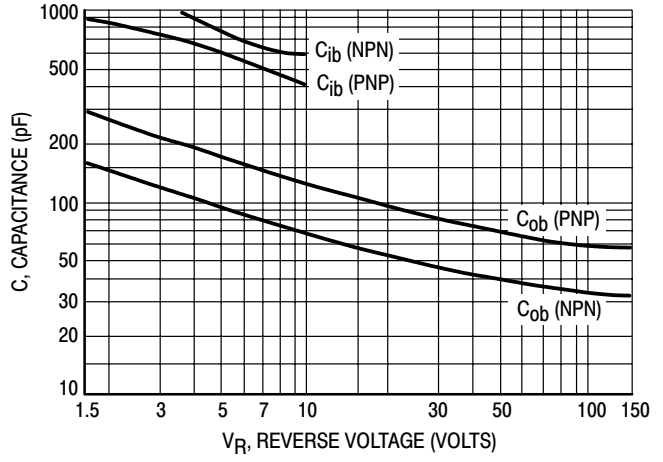
There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figures 2 and 3 is based on  $T_{J(pk)} = 150^\circ\text{C}$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} < 150^\circ\text{C}$ .  $T_{J(pk)}$  may be calculated from the data in Figure 1. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

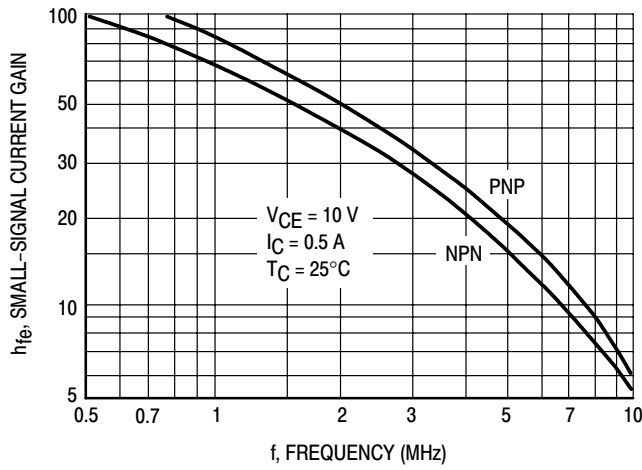
# MJF15030 MJF15031



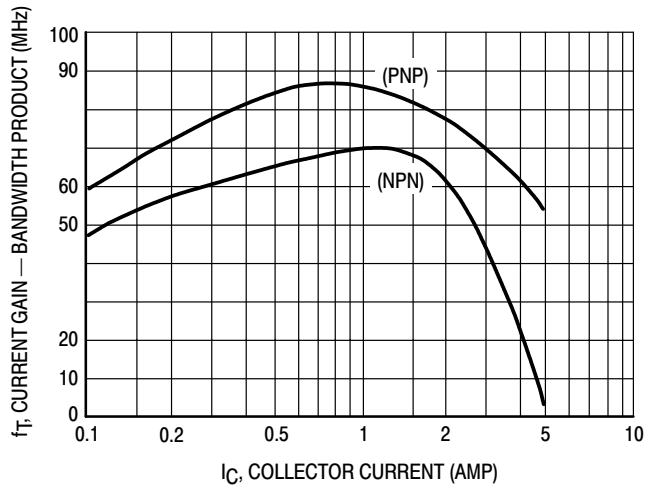
**Figure 3. Reverse Bias Switching Safe Operating Area**



**Figure 4. Capacitances**

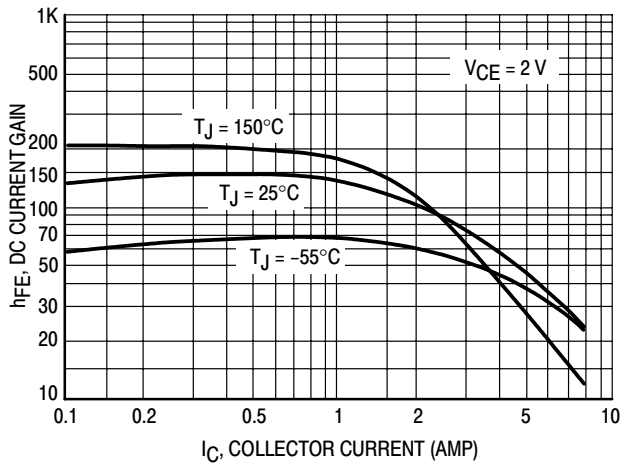


**Figure 5. Small-Signal Current Gain**

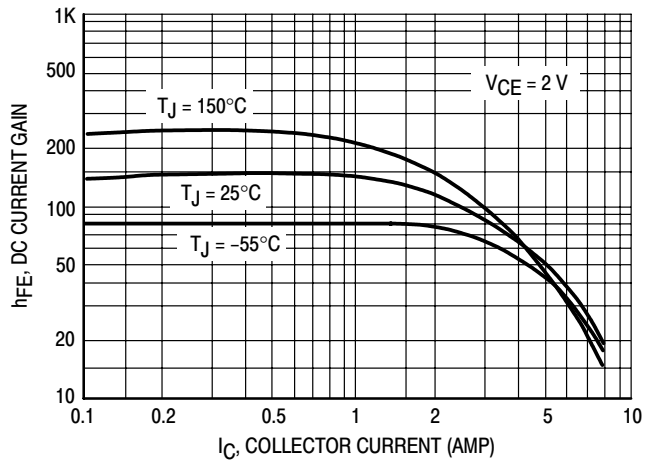


**Figure 6. Current Gain — Bandwidth Product**

## DC CURRENT GAIN



**Figure 7a. MJF15030 NPN**



**Figure 7b. MJF15031 PNP**

# MJF15030 MJF15031

## "ON" VOLTAGE

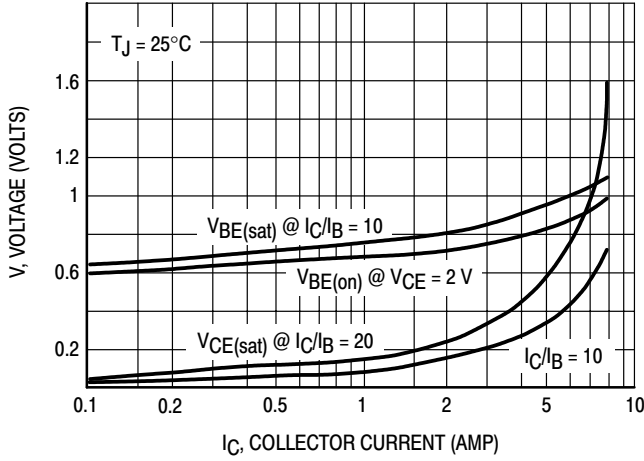


Figure 8a. MJF15030 NPN

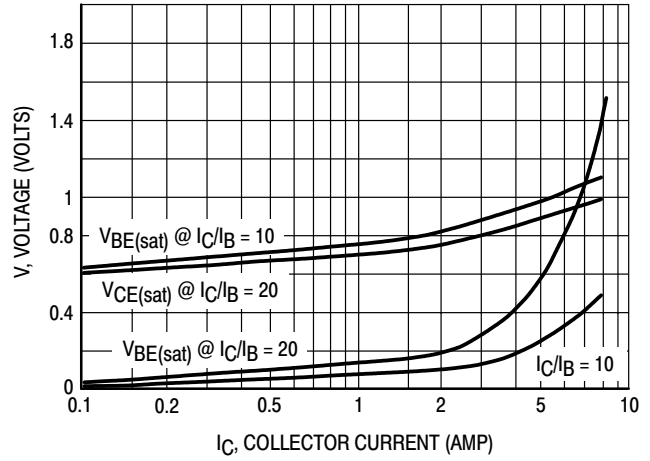


Figure 8b. MJF15031 PNP

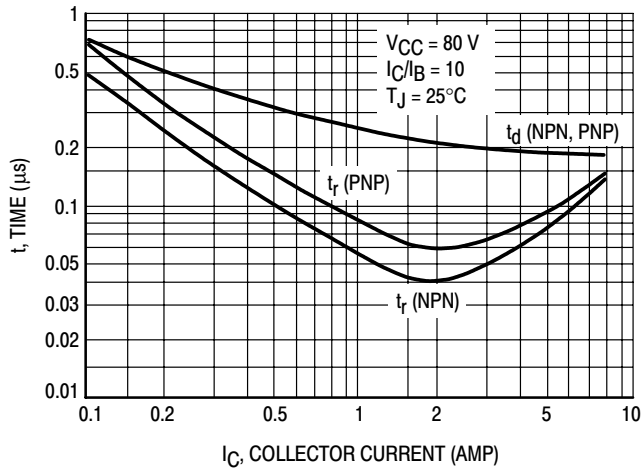


Figure 9. Turn-On Times

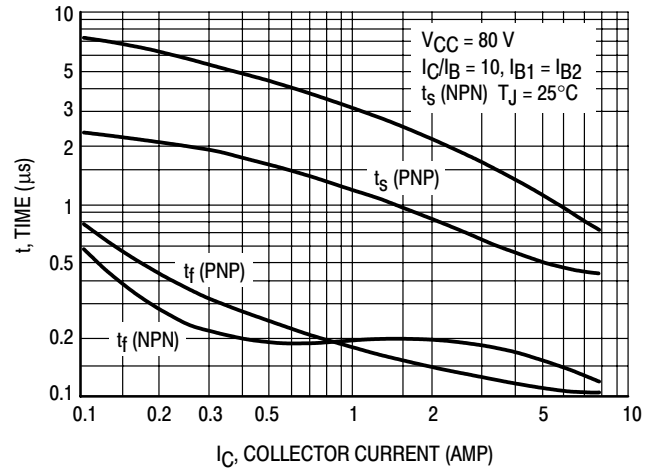
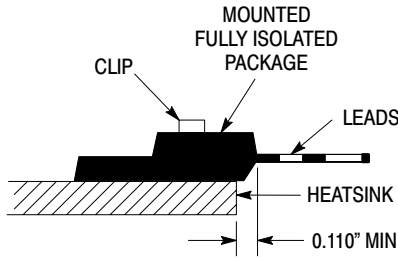


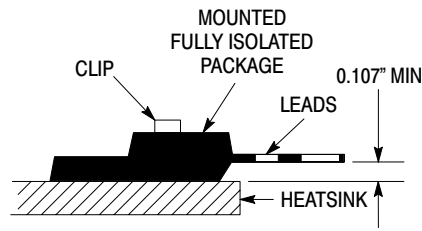
Figure 10. Turn-Off Times

# MJF15030 MJF15031

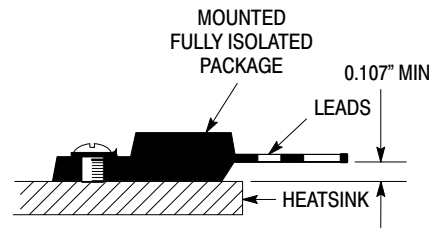
## TEST CONDITIONS FOR ISOLATION TESTS\*



**Figure 11. Clip Mounting Position for Isolation Test Number 1**



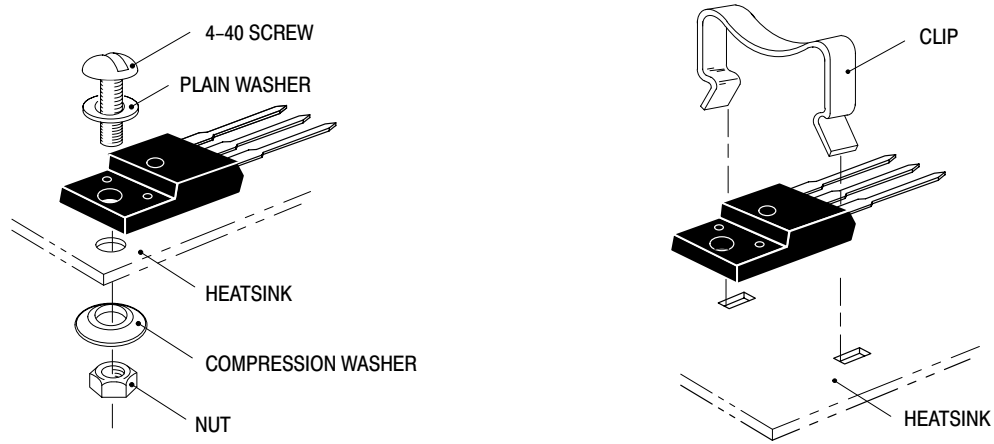
**Figure 12. Clip Mounting Position for Isolation Test Number 2**



**Figure 13. Screw Mounting Position for Isolation Test Number 3**

\*Measurement made between leads and heatsink with all leads shorted together

## MOUNTING INFORMATION



**Figure 14. Typical Mounting Techniques\***

Laboratory tests on a limited number of samples indicate, when using the screw and compression washer mounting technique, a screw torque of 6 to 8 in • lbs is sufficient to provide maximum power dissipation capability. The compression washer helps to maintain a constant pressure on the package over time and during large temperature excursions.

Destructive laboratory tests show that using a hex head 4–40 screw, without washers, and applying a torque in excess of 20 in • lbs will cause the plastic to crack around the mounting hole, resulting in a loss of isolation capability.

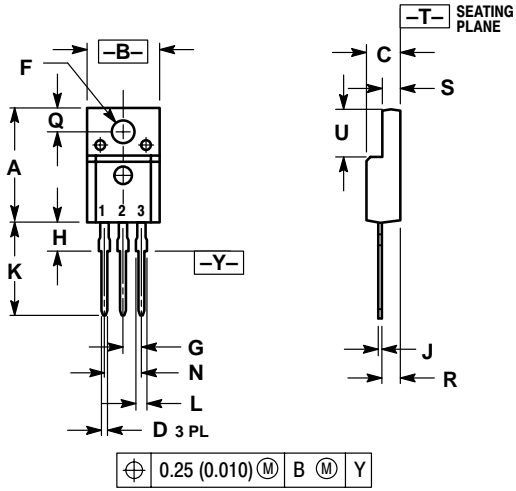
Additional tests on slotted 4–40 screws indicate that the screw slot fails between 15 to 20 in • lbs without adversely affecting the package. However, in order to positively ensure the package integrity of the fully isolated device, ON Semiconductor does not recommend exceeding 10 in • lbs of mounting torque under any mounting conditions.

\*\* For more information about mounting power semiconductors see Application Note AN1040.

# MJF15030 MJF15031

## PACKAGE DIMENSIONS

### CASE 221D-02 TO-220 TYPE ISSUE D



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.621	0.629	15.78	15.97
B	0.394	0.402	10.01	10.21
C	0.181	0.189	4.60	4.80
D	0.026	0.034	0.67	0.86
F	0.121	0.129	3.08	3.27
G	0.100 BSC		2.54 BSC	
H	0.123	0.129	3.13	3.27
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.14	1.52
N	0.200 BSC		5.08 BSC	
Q	0.126	0.134	3.21	3.40
R	0.107	0.111	2.72	2.81
S	0.096	0.104	2.44	2.64
U	0.259	0.267	6.58	6.78

- STYLE 2:  
PIN 1. BASE  
2. COLLECTOR  
3. EMITTER

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